

Low V_{CESAT} PNP Transistor

FEATURES

- Low $V_{CE(SAT)}$ -0.3 @ I_C =-2A, I_B = -200mA (Typ.)
- Complementary part with TSD882
- Epitaxial Planar Type
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC.
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
BV _{CEO}		-30	V	
BV _{CBO}		-50	V	
I _C		-3	Α	
V _{CE(SAT)}	I _C = -2A, I _B = -200mA	-0.5	V	

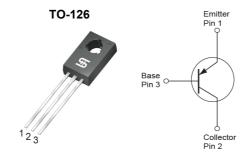






APPLICATION

- Power Supply
- Low Speed Switching Applications



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Collector-Base Voltage		V _{CBO}	-50	V	
Collector-Emitter Voltage		V _{CEO}	-30	V	
Emitter-Base Voltage		V _{EBO}	-5	V	
Collector Current	DC	I _C	-3		
	Pulse		-7 (note)	Α	
Collector Power Dissipation	T _A = 25°C	P _D	1	W	
	$T_C = 25^{\circ}C$		10		
Operating Junction Temperature		T _J	+150	°C	
Operating Junction and Storage Temperature Range		T _{STG}	- 55 to +150	°C	

Note: Single pulse, Pw≤350µs, Duty≤2%

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	6.25	°C/W	

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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$I_{C} = -50\mu A, I_{E} = 0$	BV _{CBO}	-50			V
Collector-Emitter Breakdown Voltage	$I_{\rm C} = -1 \text{mA}, I_{\rm B} = 0$	BV _{CEO}	-30			V
Emitter-Base Breakdown Voltage	$I_E = -50 \mu A, I_C = 0$	BV _{EBO}	-5			V
Collector Cutoff Current	$V_{CB} = -30V, I_{E} = 0$	I _{CBO}			-1	μA
Emitter Cutoff Current	$V_{EB} = -33V$, $I_{C} = 0$	I _{EBO}			-1	μΑ
Collector-Emitter Saturation Voltage	$I_C = -2A, I_B = -200 \text{mA}$	*V _{CE(SAT)}		-0.3	-0.5	V
Base-Emitter Saturation Voltage	$I_C = -2A$, $I_B = -200 \text{mA}$	*V _{BE(SAT)}		-1	-2	V
DC Current Transfer Ratio	$V_{CE} = -2V, I_{C} = -1A$	*h _{FE}	100		500	
Transition Frequency	V_{CE} =-5V, I_{C} =-100mA, f=100MHz	f _⊤		80		MHz
Output Capacitance	V _{CB} = -10V, f=1MHz	Cob		55		pF
Collector Cutoff Current	$V_{CB} = -30V, I_{E} = 0$	I _{CBO}			-1	μA

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ORDERING INFORMATION

PART NO.	PACKAGE	PACKING		
TSB772CK B0G	TO-126	250pcs / Bulk Bag		
TSB772CK C0G	TO-126	50pcs / Tube		

^{*} Pulse Test: Pulse Width ≤380µS, Duty Cycle≤2%



ELECTRICAL CHARACTERICS CURVES (T_A=25°C, unless otherwise noted)

Figure 1. DC Current Gain

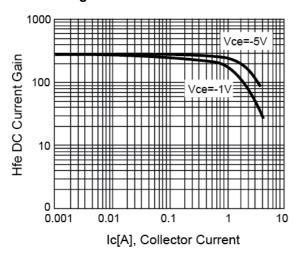


Figure 3. V_{BE(SAT)} vs. Collector Current

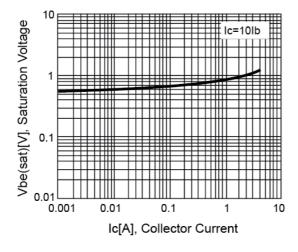


Figure 2. V_{CE(SAT)} vs. Collector Current

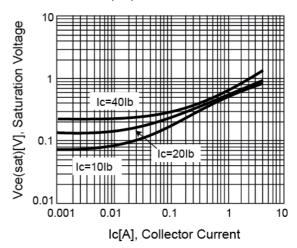
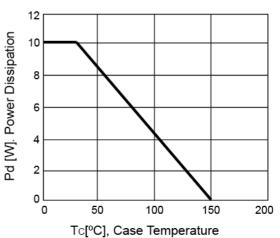


Figure 4. Power Derating Curve



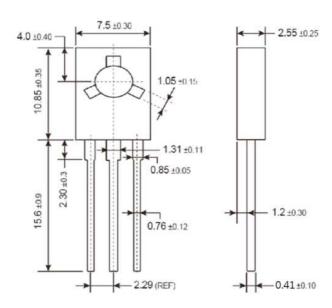
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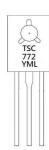


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

TO-126



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

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L = Lot Code



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